

(9) Lee-suk-kyun.in.  
(27) gate with (slant\$4 adj2 (sidewall or (side adj w  
(26) (gate with (slant\$4 adj2 (sidewall or (side adj  
(18) ((gate with (slant\$4 adj2 (sidewall or (side adj  
(16) (((gate with (slant\$4 adj2 (sidewall or (side ac  
(2) (((gate with (slant\$4 adj2 (sidewall or (side ac  
(14) (((gate with (slant\$4 adj2 (sidewall or (side ac  
(12) ((gate with (slant\$4 adj2 (sidewall or (side adj

USPAT, US-PGPUB, EPO, JPO, BM, TDB

Default operator:

☐ Plurals  
☐ Highlight all hit terms initially

99 and ("MOS" or "DMOS" or memory)

	U	I	PT	P	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R	Inventor	S	C
1					US 20020000380 A1	20020103	43	METHOD, CHEMISTRY, AND APPARATUS FOR NOBLE METAL ELECTROPLATING ON A MICROELECTRONIC WORKPIECE	205/102	204/212; 204/222; 204/224R;		GRAHAM, LYNDON W. et al.		
2					US 20020052098 A1	20020502	16	Method of fabricating gate	438/585	257/E21.578; 438/637; 438/640;		Chang, Ching-Yu		
3					US 20020063275 A1	20020530	19	Method of forming transistor gate	257/315	257/317; 257/E21.209; 257/E29.129;		Chang, Ching-Yu		
4					US 20020121657 A1	20020905	25	Double-bit non-volatile memory structure and corresponding method of manufacture	257/296	257/202; 257/390; 257/401;		Chen, Chin-Yang		
5					US 20020142547 A1	20021003	16	Method of fabricating gate	438/257	257/315; 257/330; 257/E21.578;		Chang, Ching-Yu		
6					US 20020177285 A1	20021128	16	Semiconductor power component and a corresponding manufacturing method	438/309	257/E21.383; 257/E29.066; 257/E29.198		Feiler, Wolfgang et al.		
7					US 20030020928 A1	20030130	85	Methods and apparatus for processing microelectronic workpieces using metrology	356/630			Ritzdorf, Thomas L. et al.		
8					US 20030032142	20030130	25	Double-bit non-volatile memory structure and manufacturing method	438/257	257/E21.682; 257/E21.102;		Chen, Chin-Yang		